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<div style="border: 2px solid black; border-radius: 50%; padding: 10px; display: inline-block;"><div style="text-align: center;">INFORMATION DISCLOSURE CITATION <small>(Use several sheets if necessary)</small></div><div style="text-align: center;">DEC. 8 2004 PATENT & TRADEMARK OFFICE</div></div>				ATTY DOCKET NO. YOR920030077US1		APPLICATION NO. 10/627,753	
				APPLICANT(S) Kam-Leung Lee, et al.			
				FILING DATE July 28, 2003		GROUP ART UNIT 2823	
				U.S. PATENT DOCUMENTS			
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
<i>bu</i>	6,518,150 B1	02/11/03	Matsumoto				
<i>bu</i>	6,069,062	05/30/00	Downey				
<i>bu</i>	6,180,476 B1	01/30/01	Yu				
<i>bu</i>	6,380,053 B1	04/30/02	Komatsu				
U.S. PATENT APPLICATION PUBLICATIONS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
	2003/009640 A1	05/22/03	Borland, et al.				
<div style="border: 1px solid black; width: 40px; height: 40px; margin: 5px; transform: rotate(45deg); transform-origin: center;"></div>	<i>document cannot be found</i>						
FOREIGN PATENT DOCUMENTS							
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
<i>bu</i>		Article by T.H. Huang, et al.: "Influence of Fluorine Preamorphization on the Diffusion and Activation of Low-Energy Implanted Boron During Rapid Thermal Annealing", Applied Physics Letters, American Institute of Physics, NY, US Vol. 65, No. 14, October 3, 1994, pp. 1829-1831.					
<i>bu</i>		Article by S. Saito, et al.: "Defect Reduction by MeV ion Implantation for Shallow Junction Formation", Applied Physics Letters, American Institute of Physics, Vol. 63, No. 2, July 12, 1993, pp. 197-199.					
EXAMINER <i>Brook Kehede</i>			DATE CONSIDERED <i>1/6/2005</i>				
<small>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>							

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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Bu	6,426,278 B1	07/30/02	Nowak, et al.			
Bu	6,087,209	07/11/00	Yeap, et al.			
Bu	6,410,393 B1	06/25/02	Hao, et al.			

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*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
Bu	WO 97/42652	11/13/97	PCT				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

Bu	PCT International Search Report dated October 8, 2004.
Bu	PCT Written Opinion of the International Searching Authority. (EPO - January 2004)

EXAMINER	DATE CONSIDERED
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